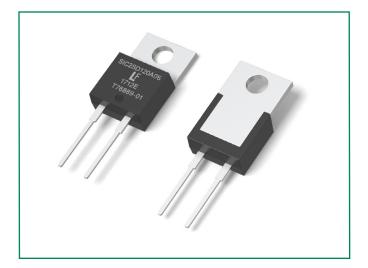


LSIC2SD120A05









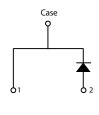
Description

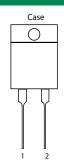
This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-220-2L





Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "PB-free" logo = PB-free lead plating

Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	1200	V	
DC Blocking Voltage	V _R	T _i = 25 °C	1200	V	
	I _F	T _c = 25 °C	17.5		
Continuous Forward Current		T _C = 135 °C	8.5	Α	
		T _C = 158 °C	5		
Non-Repetitive Forward Surge Current	I _{FSM}	$T_C = 25 ^{\circ}\text{C}, T_P = 10 \text{ms}, \text{Half sine pulse}$	40	А	
Power Dissipation	D	T _c = 25 °C	100	W	
rower dissipation	P _{Tot}	T _c = 110 °C	43.3	V V	
Operating Junction Temperature	T _J	-	-55 to 175	°C	
Storage Temperature	T _{STG}	-	-55 to 150	°C	
Soldering Temperature (reflow MSL 1)	Т	-	260	°C	

GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L

Electrical Characteristics

	Symbol	Conditions	Value			
Characteristics			Min.	Тур.	Max.	Unit
Forward Voltage	V _F	I _F = 5 A, T _J = 25 °C	-	1.5	1.8	V
		I _F = 5 A, T _J = 175 °C	-	2.1		V
Reverse Current	I _R	$V_{R} = 1200 V, T_{J} = 25 ^{\circ}C$	-	<1	100	μΑ
		V _R = 1200 V , T _J = 175 °C	-	5		
Total Capacitance	С	$V_R = 1 V$, $f = 1 MHz$	-	310		
		V _R = 400 V, f = 1 MHz	-	29		pF
		$V_{R} = 800 V, f = 1 MHz$	-	21		
Total Capacitive Charge	O _C	$V_R = 800 \text{ V}, \ \ Q_C = \int\limits_0^{V_R} c(v) dv$	-	30		nC

Footnote: T₁ = +25 °C unless otherwise specified

Thermal Characteristics

Characteristics		2				
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Thermal Resistance	R _{euc}	-	-	1.50		°C/W

Figure 1: Typical Foward Characteristics

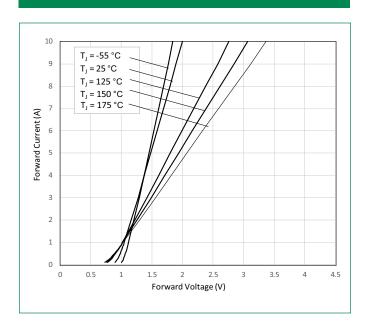


Figure 2: Typical Reverse Characteristics

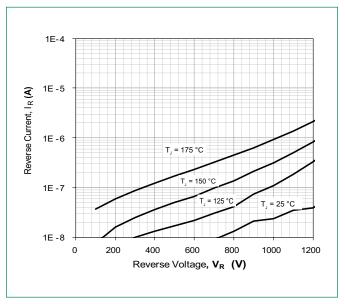




Figure 3: Power Derating

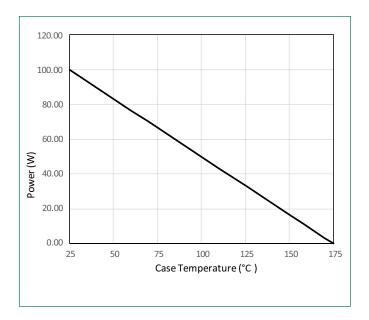


Figure 4: Current Derating

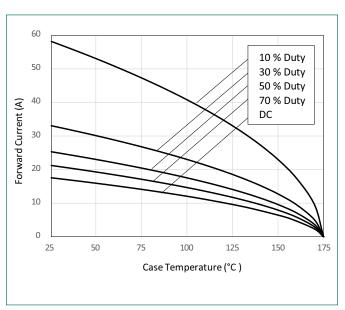


Figure 5: Capacitance vs. Reverse Voltage

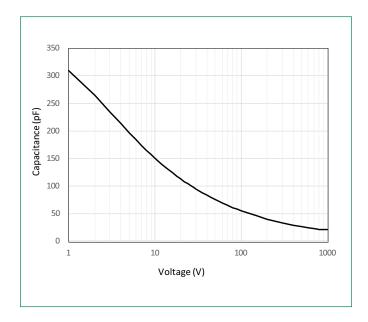
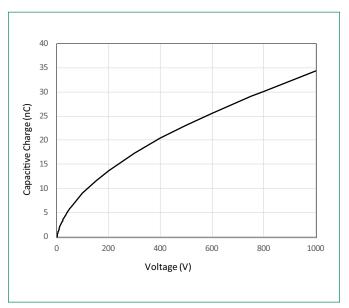


Figure 6: Capacitive Charge vs. Reverse Voltage



GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L

Figure 7: Stored Energy vs. Reverse Voltage

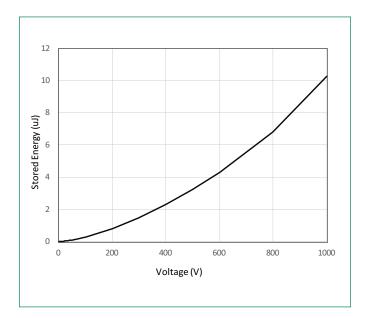
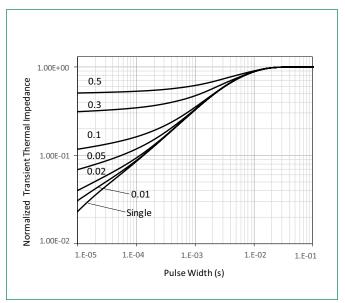
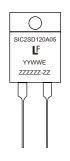


Figure 8: Transient Thermal Impedance



Part Numbering and Marking System



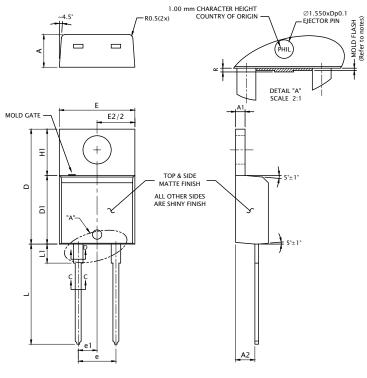
SIC = SiC Diode = Gen2 SD = Schottky Diode 120 = Voltage Rating (1200 V) = TO-220-2L = Current Rating (5 A) 05 ΥY = Year WW = Week = Special Code ZZZZZZ-ZZ = Lot Number

Packing Options

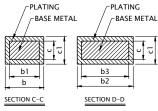
Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD120A05	SIC2SD120A05	Tube	1000



Dimensions-Package TO-220-2L



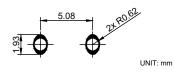
Symbol	Millimeters				
Syllibol	Min	Nominal	Max		
А	4.320	4.450	4.570		
A1	1.140	1.270	1.400		
A2	2.500	-	2.740		
b	0.690	-	0.880		
b1	0.680	-	0.870		
b2	1.230	-	1.390		
b3	1.220	1.270	1.380		
С	0.360	-	0.503		
с1	0.630	-	0.527		
D	14.900	-	15.600		
D1	8.615	-	9.017		
D2	12.840	-	12.950		
Е	10.000	10.180	10.360		
E1	7.570	7.610	7.680		
e1	2.490	2.540	2.590		
е	5.030	5.080	5.130		
H1	6.295	6.545	6.795		
L	13.000	13.500	14.00		
L1	2.390	-	3.250		
øΡ	3.710	3.840	3.960		
Q	2.650	-	3.050		
R	-	-	0.254		



D2

ď

Recommended Solder Pad Layout

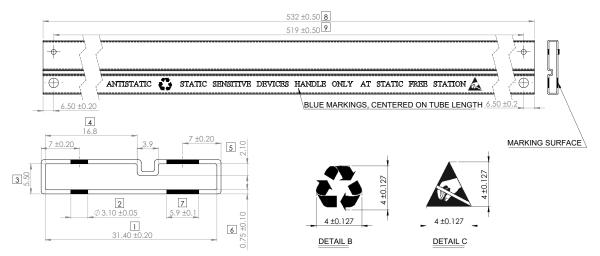




- DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.127 MM PER SIDE.
 THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF PLASTIC BODY.
- 2. DIMENSIONS E2 & H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES RE ALLOWED.

GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L

Packing Specification (Tube for TO-220-2L)



- NOTES:

 1. Material transparent extruded PVC with antistatic dipping

 2. Radius: 0.5 maximum unless otherwisen specified

 3. Critical areas: Labelled in Box

 4. All pin plugh poles are considered critical dimension

 5. Marking Font Type: Times new roman, 3.12 ±0.127 in height

 6. Material Thickness: 0.75 ±0.10

 7. Tolerance unless otherwise specified: Decimal: ±0.05 Angle: ±1°

 8. Unit: Millimeter (mm)

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